

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
		S11 AND S\$	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 13:36
S1	2	("5912839").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 13:34
S2	2	("6141241").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/29 12:58
S3	586	stanford ovshinsky.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/08/29 13:16
S4	182	365/163.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:42
S5	70079	secur\$3 ADJ (device OR element)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 13:51
S6	355	("phase change" OR phase-change) ADJ (device OR element)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 14:06
S7	2	S5 AND S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 13:52

S8	5710	("phase change" OR phase-change) ADJ (device OR element OR material)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 14:06
S9	16	S5 AND S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/29 14:06
S10	3016	transistor AND ("phase change" phase-change) AND parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 13:35
S11	91	transistor SAME ("phase change" phase-change) SAME parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:31
S12	183	365/163.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 13:36
S13	5	S11 AND S12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 13:36
S14	470	resist\$4 SAME ("phase change" phase-change) SAME parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:31
S15	478	transistor SAME amorphous SAME parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:23

S16	4	S12 AND S15	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:14
S17	789	resist\$4 SAME amorphous SAME parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:16
S18	3	S12 AND S17	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:17
S19	5002	transistor SAME (register OR weight\$3) SAME parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:29
S20	3561	transistor SAME register SAME parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:25
S21	1609	transistor SAME weight\$3 SAME parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:27
S22	1	S12 AND (S20 OR S21)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:26
S23	1	S19 SAME ("phase chang\$3" phase-chang\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:30

S24	13	transistor SAME ("phase chang\$3" phase-chang\$3) SAME parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:31
S25	46	resist\$4 SAME ("phase chang\$3" phase-chang\$3) SAME parallel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/08/30 14:31
S26	2	("20020036931").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/30 14:42
S27	1	("multi terminal" multi-terminal) ADJ ("phase chang\$3" phase-chang\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:28
S28	1	("multi terminal" multi-terminal) SAME ("phase chang\$3" phase-chang\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/01 16:29
S29	3	("6480438" "6590907" "6707712").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/09/02 09:29
S30	0	("6862214").URPN.	USPAT	OR	ON	2005/09/02 09:32
S31	173	terminal SAME ("phase chang\$3" phase-chang\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 16:24
S32	77	("phase chang\$3" phase-chang\$3) SAME register	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/02 13:29
S33	10	("three terminal" three-terminal) SAME ("phase chang\$3" phase-chang\$3)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 16:32

S34	84	("three terminal" three-terminal) SAME amorphous	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/06 16:32
S35	108	("three terminal" three-terminal) SAME ("memory device")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:33
S36	2	("6750469").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 15:41
S37	26058	resistance SAME (crystalline off set) SAME (amorphous on reset)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:58
S38	480209	resistance SAME (crystalline off set)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:58
S39	4756	register SAME encrypt\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/08 14:33
S40	1226	register SAME encrypt\$3 SAME memory	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/08 14:33
S41	230	257/2.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/09 10:42